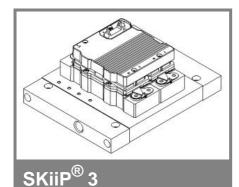
### SKiiP 1203GB172-2DW V3



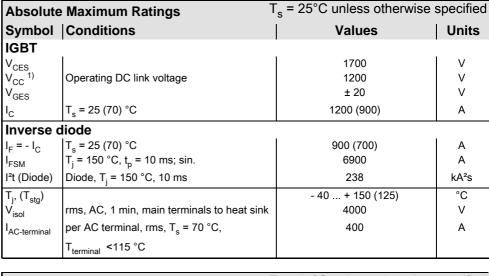
# 2-pack-integrated intelligent Power System

### Power section SKiiP 1203GB172-2DW V3

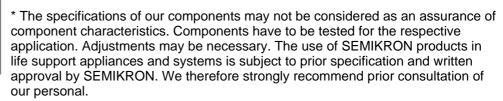
**Preliminary Data** 

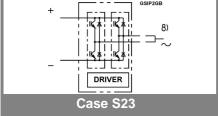
#### **Power section features**

- SKiiP technology inside
- Trench IGBTs
- CAL diode technology
- · Integrated current sensor
- Integrated temperature sensor
- Integrated heat sink
- IEC 60721-3-3 (humidity) class 3K3/IE32 (SKiiP<sup>®</sup> 3 System)
- IEC 60068-1 (climate) 40/125/56
- UL recognized file no. E63532
- with assembly of suitable MKP capacitor per terminal (SEMIKRON type is recommended)
- AC connection busbars must be connected by the user; copper busbars available on request

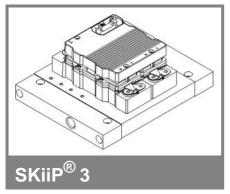


Characteristics				T <sub>s</sub> = 25°C unless otherwise specified				
Symbol	Conditions				min.	typ.	max.	Units
IGBT								
V <sub>CEsat</sub>	I <sub>C</sub> = 600 A measured at	A, T <sub>j</sub> = 25 (1 terminal	25) °C;			1,9 (2,2)	2,4	V
$V_{CEO}$	$T_i = 25 (12)$	25) °C; at te	erminal			1 (0,9)	1,2 (1,1)	V
$r_{CE}$	1 1 '	25) °C; at te				1,5 (2,1)	1,9 (2,5)	mΩ
I <sub>CES</sub>	$V'_{GE} = 0 \text{ V}, V_{CE} = V_{CES},$ $T_i = 25 (125) ^{\circ}C$					2,4 (144)		mA
E <sub>on</sub> + E <sub>off</sub>	$I_C = 600 \text{ A}, V_{CC} = 900 \text{ V}$					mJ		
	T <sub>j</sub> = 125 °C, V <sub>CC</sub> = 1200 V					mJ		
R <sub>CC+EE</sub>	terminal chip, T <sub>i</sub> = 25 °C				mΩ			
L <sub>CE</sub>	top, bottor	top, bottom				6		nΗ
C <sub>CHC</sub>	per phase, AC-side				2		nF	
Inverse o	diode							
$V_F = V_{EC}$	I <sub>F</sub> = 600 A measured at	, T <sub>j</sub> = 25 (1 terminal	25) °C			2 (1,8)	2,15	V
$V_{TO}$	T <sub>i</sub> = 25 (12	25) °C				1,1 (0,8)	1,2 (0,9)	V
r <sub>T</sub>	$T_i = 25 (12)$					1,5 (1,7)	1,6 (1,8)	mΩ
Ė <sub>rr</sub>		, V <sub>CC</sub> = 90	0 V			72		mJ
	T <sub>j</sub> = 125 °	C, V <sub>CC</sub> = 12	200 V			86		mJ
Mechani	cal data							
$M_{dc}$	DC terminals, SI Units				6		8	Nm
$M_{ac}$	AC terminals, SI Units				13		15	Nm
W	SKiiP® 3 System w/o heat sink					1,7		kg
W	heat sink					4,3		kg
						c.); "s" re		
		e to bui	lt-in tem	perature	sensor	(acc. IEC		rī I
R <sub>th(j-s)I</sub>	per IGBT						0,026	K/W
R <sub>th(j-s)D</sub>	per diode					tau	0,05	K/W
$Z_{th}$	R <sub>i</sub> (mK/W) (max. values)				l 4			
7	1	2	3	4	1	2	3	4
Z <sub>th(j-r)l</sub>	2,8 4	11,6 6	13,6 26	0 26	69 50	0,35 5	0,02 0,25	1 0,04
Z <sub>th(j-r)D</sub>	5,5	4,8	1,1	0,6	48		2,8	0,04
$Z_{th(r-a)}$	٥,٥	4,0	1,1	0,0	40	10	۷,0	0,4





## SKiiP 1203GB172-2DW V3



## 2-pack-integrated intelligent Power System

2-pack integrated gate driver SKiiP 1203GB172-2DW V3

**Preliminary Data** 

#### **Gate driver features**

- CMOS compatible inputs
- Wide range power supply
- Integrated circuitry to sense phase current, heat sink temperature
- · Short circuit protection
- · Over current protection
- Over voltage protection (option)
- Power supply protected against under voltage
- · Interlock of top/bottom switch
- Isolation by transformers
- Fibre optic interface (option for GB-types only)
- IEC 60068-1 (climate) 40/85/56)

Absolute	Maximum Ratings	T <sub>a</sub> = 25°C unless otherwise specified		
Symbol	Conditions	Values	Units	
$V_{S2}$	unstabilized 24 V power supply	30	V	
$V_{i}$	input signal voltage (high)	15 + 0,3	V	
dv/dt	secondary to primary side	75	kV/μs	
$V_{isollO}$	input / output (AC, rms, 2s)	4000	V	
V <sub>isolPD</sub>	partial discharge extinction voltage, rms, Q <sub>PD</sub> ≤10 pC;	1500	V	
V <sub>isol12</sub>	output 1 / output 2 (AC, rms, 2s)	1500	V	
f <sub>sw</sub>	switching frequency	14	kHz	
$f_{out}$	output frequency for I <sub>peak(1)</sub> =I <sub>C</sub>	14	kHz	
$T_{op} (T_{stg})$	operating / storage temperature	- 40 + 85	°C	

Characte	eristics	(T <sub>a</sub> = 25°C)			
Symbol	Conditions	min.	typ.	max.	Units
$V_{S2}$	supply voltage non stabilized	13	24	30	V
I <sub>S2</sub>	V <sub>S2</sub> = 13V - 30V	210+29*f/kHz+0,00023*(I <sub>AC</sub> /A) <sup>2</sup>			mA
V <sub>iT+</sub>	input threshold voltage (High)			12,3	V
$V_{iT-}$	input threshold voltage (Low)	4,6			V
R <sub>IN</sub>	input resistance		10		kΩ
C <sub>IN</sub>	input capacitance		1		nF
t <sub>d(on)IO</sub>	input-output turn-on propagation time		1,4		μs
t <sub>d(off)IO</sub>	input-output turn-off propagation time		1,4		μs
t <sub>pERRRESET</sub>	error memory reset time		12,2		μs
$t_{TD}$	top / bottom switch interlock time		3,3		μs
I <sub>analogOUT</sub>	max. 5mA; 8 V corresponds to 15 V supply voltage for external components		1000		Α
I <sub>s1out</sub>	max. load current			50	mA
I <sub>TRIPSC</sub> $T_{tp}$ $U_{DCTRIP}$	over current trip level (I <sub>analog</sub> OUT = 10 V) over temperature protection U <sub>DC</sub> -protection ( U <sub>analog OUT</sub> = 9 V);	110	1250 not implemented	120	A °C V
	(option for GB types)				

For electrical and thermal design support please use SEMISEL. Access to SEMISEL is via SEMIKRON website http://www.semikron.com.

\* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.

